STGW45NC60WD

45 A - 600 V ultra fast IGBT

Features

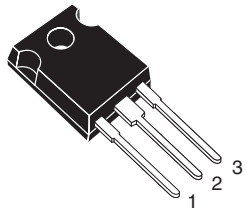
- Low C_{RES} / C_{IES} ratio (no cross conduction susceptibility)
- Very soft ultra fast recovery anti parallel diode

Applications

- High frequency inverters, UPS
- Motor drivers
- HF, SMPS and PFC in both hard switch and resonant topologies
- Welding
- Induction heating

Description

This IGBT utilizes the advanced Power MESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.



TO-247 long leads

Figure 1. Internal schematic diagram

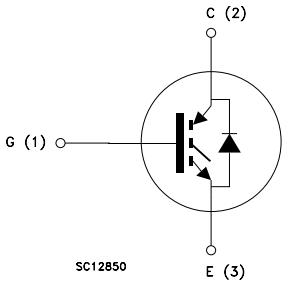


Table 1. Device summary

Order code	Marking	Package	Packaging
STGW45NC60WD	GW45NC60WD	TO-247 long leads	Tube

Contents

1 Electrical ratings 3

2 Electrical characteristics 4

2.1 Electrical characteristics (curves) 7

3 Test circuit 10

4 Package mechanical data 11

5 Revision history 13

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GS} = 0)	600	V
I_C (1)	Collector current (continuous) at T_C=25 °C	90	A
I_C (1)	Collector current (continuous) at T_C=100 °C	45	A
I_{CL} (2)	Turn-off latching current	230	A
I_{CP}(3)	Pulsed collector current	230	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Diode RMS forward current at T_C=25 °C	30	A
I_{FSM}	Surge non repetitive forward current t_p=10 ms sinusoidal	120	A
P_{TOT}	Total dissipation at T_C = 25 °C	285	W
T_j	Operating junction temperature	– 55 to 150	°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. V_{clamp} = 80% V_{CES} , Tj = 150 °C, R_G = 10 Ω, V_{GE}= 15 V
3. Pulse width limited by max junction temperature allowed

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case IGBT	0.437	°C/W
$R_{thj\text{-}case}$	Thermal resistance junction-case diode	1.5	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	50	°C/W

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. Static (electrical characteristics)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage (V_{GE} = 0)	I_C = 1 mA	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}= 15 V, I_C= 30 A V_{GE}= 15 V, I_C= 30 A, Tc= 125 °C		2.1 1.9	2.6	V V
$V_{GE(th)}$	Gate threshold voltage	V_{CE}= V_{GE}, I_C= 250 µA	3.75		5.75	V
I_{CES}	Collector-emitter leakage current (V_{GE} = 0)	V_{CE} = 600 V V_{CE} = 600 V, Tc=125 °C			500 5	µA mA
I_{GES}	Gate-emitter leakage current (V_{CE} = 0)	V_{GE} = ± 20 V			±100	nA
g_{fs} (1)	Forward transconductance	V_{CE} = 15 V, I_C= 30 A		20		S

1. Pulsed: pulse duration = 300 ìs, duty cycle 1.5%

Table 5. Dynamic (electrical characteristics)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies} C_{oes} C_{res}	Input capacitance Output capacitance Reverse transfer capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE}= 0		2900 298 59		pF pF pF
Q_g Q_{ge} Q_{gc}	Total gate charge Gate-emitter charge Gate-collector charge	V_{CE} = 390 V, I_C = 30 A, V_{GE} = 15 V, *(see Figure 18)*		126 16 46		nC nC nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390 V, I_C = 30 A R_G= 10 Ω, V_{GE}= 15 V, *(see Figure 17)*		33 12 2600		ns ns A/µs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_C = 30A R_G= 10Ω, V_{GE}= 15V, T_C= 125 °C *(see Figure 17)*		32 14 2300		ns ns A/µs
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390 V, I_C = 30 A, R_{GE} = 10 Ω, V_{GE} =15 V, *(see Figure 17)*		26 168 36		ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390 V, I_C = 30 A, R_{GE}=10 Ω, V_{GE} =15 V, T_C=125 °C *(see Figure 17)*		54 213 67		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on} (1) E_{off} (2) E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390 V, I_C = 30 A R_G= 10 Ω, V_{GE}= 15 V, *(see Figure 17)*		302 349 651		µJ µJ µJ
E_{on} (1) E_{off} (2) E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390 V, I_C = 30 A R_G= 10 Ω, V_{GE}= 15 V, T_C = 125 °C *(see Figure 17)*		553 750 1303		µJ µJ µJ

1. Eon is the turn-on losses when a typical diode is used in the test circuit in *Figure 20* Eon include diode recovery energy. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
V_F	Forward on-voltage	I_F = 30 A I_F = 30 A, T_C = 125 °C		2.4 1.8		V V
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_F = 30 A, V_R = 50 V, di/dt =100 A/µs *(see Figure 20)*		45 56 2.55		ns nC A
t_{rr} Q_{rr} I_{rrm}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_F = 30 A, V_R = 50 V, T_C= 125 °C, di/dt =100 A/µs *(see Figure 20)*		100 290 5.8		ns nC A

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

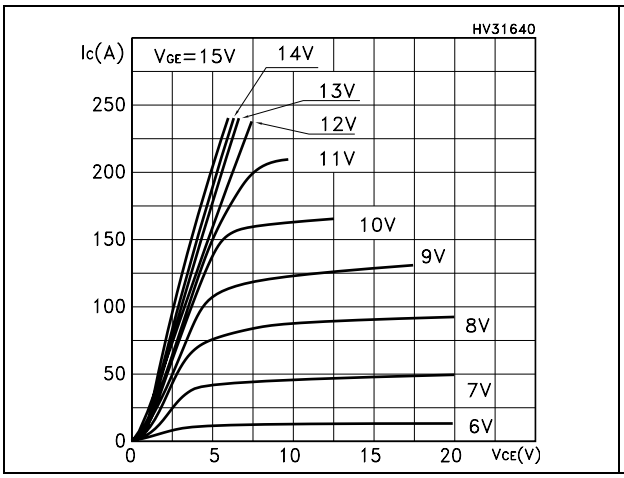


Figure 3. Transfer characteristics

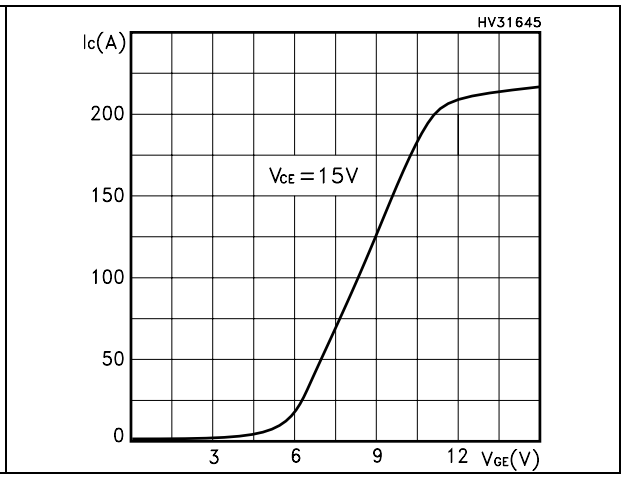


Figure 4. Transconductance

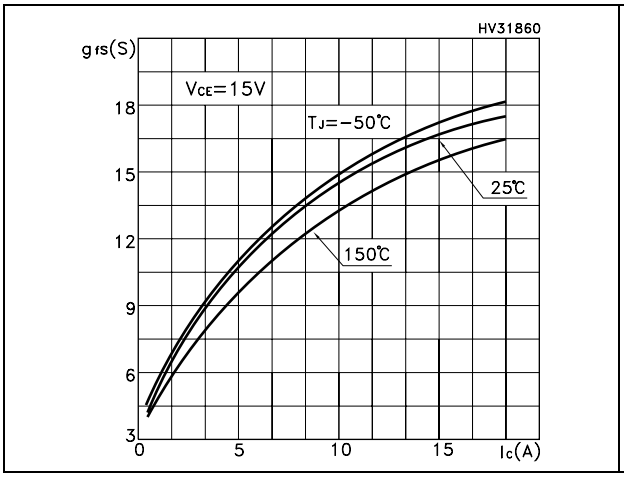


Figure 5. Collector-emitter on voltage vs temperature

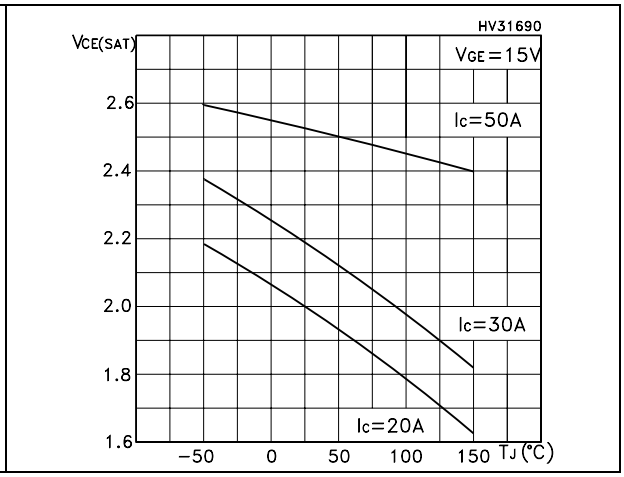


Figure 6. Collector-emitter on voltage vs collector current

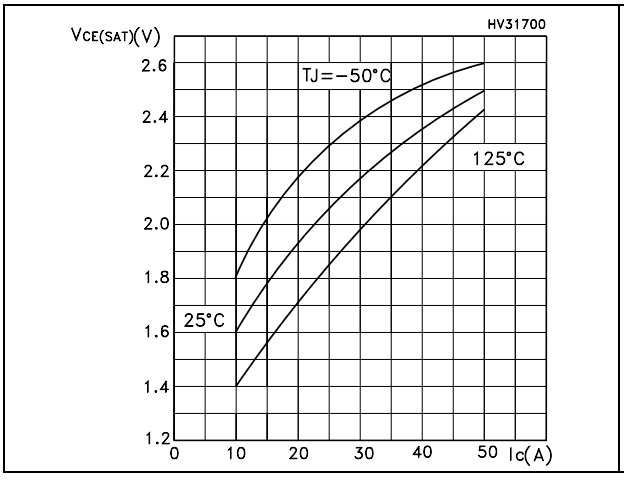


Figure 7. Normalized gate threshold vs temperature

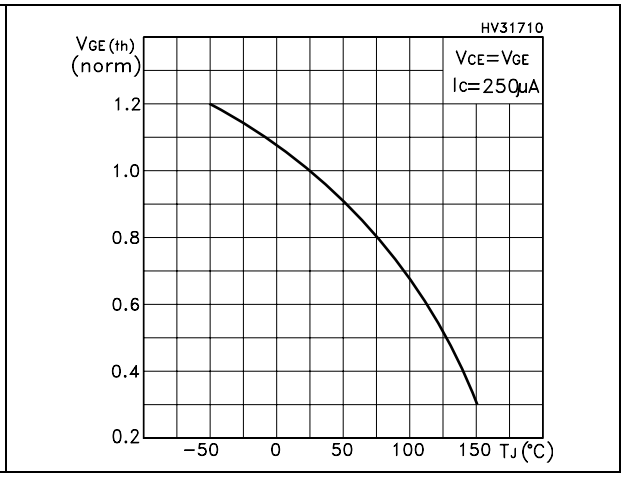


Figure 8. Normalized breakdown voltage vs temperature

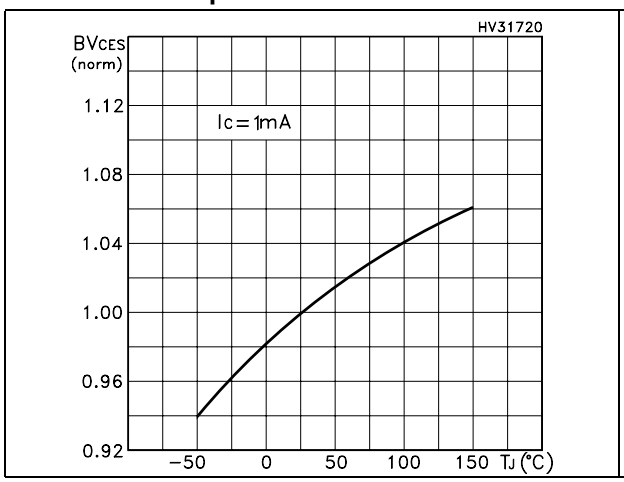


Figure 9. Gate charge vs gate-emitter voltage

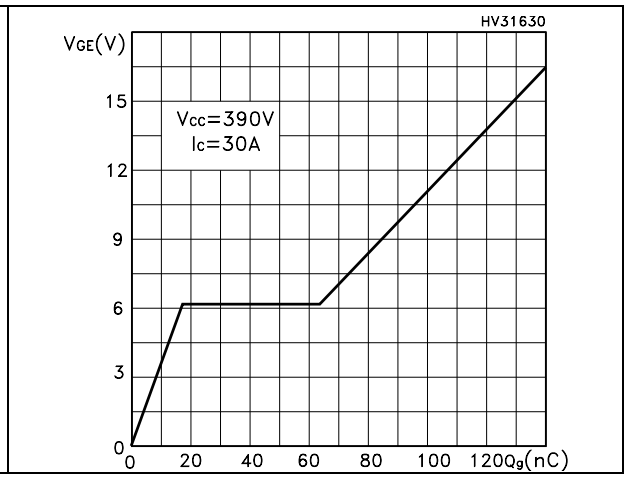


Figure 10. Capacitance variations

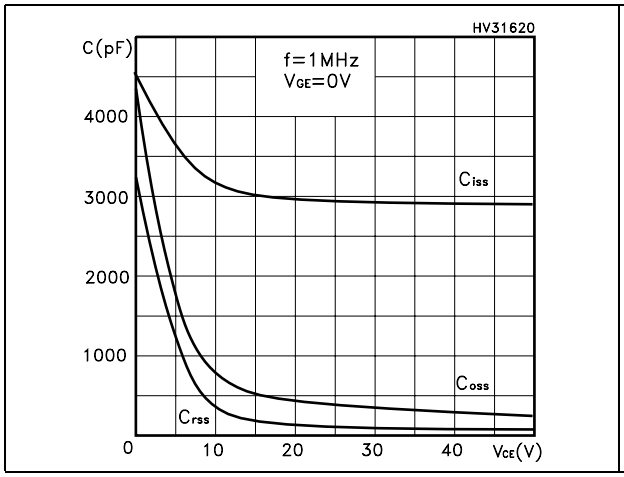


Figure 11. Switching losses vs temperature

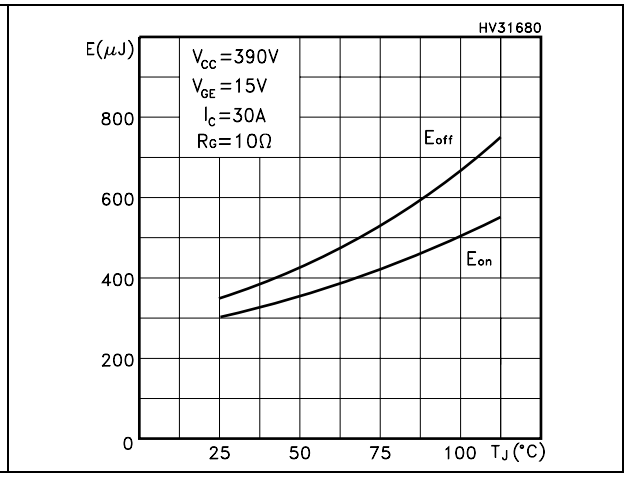


Figure 12. Switching losses vs gate resistance

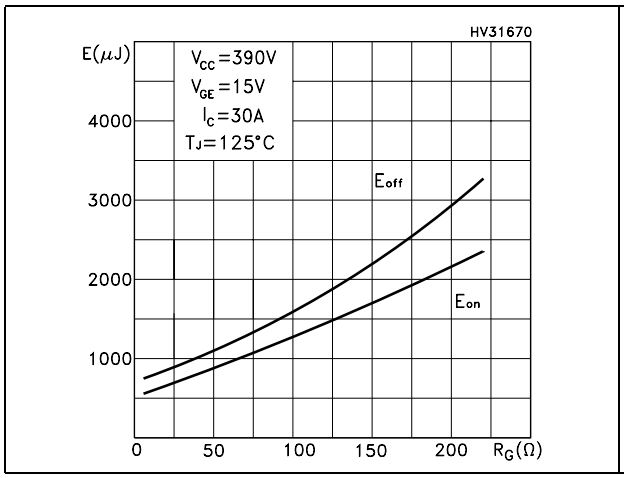


Figure 13. Switching losses vs collector current

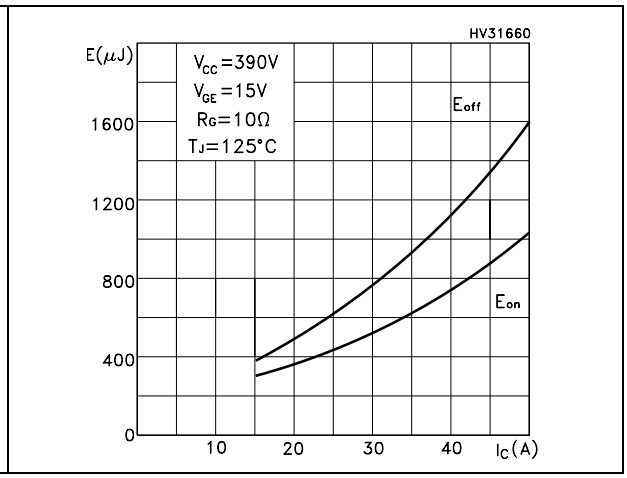


Figure 14. Thermal impedance

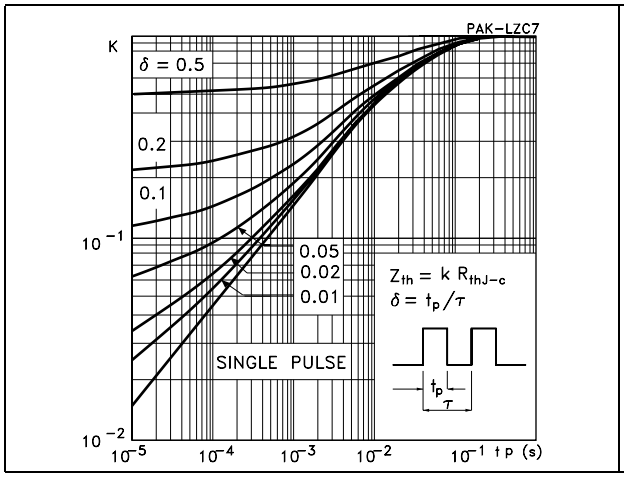


Figure 15. Turn-off SOA

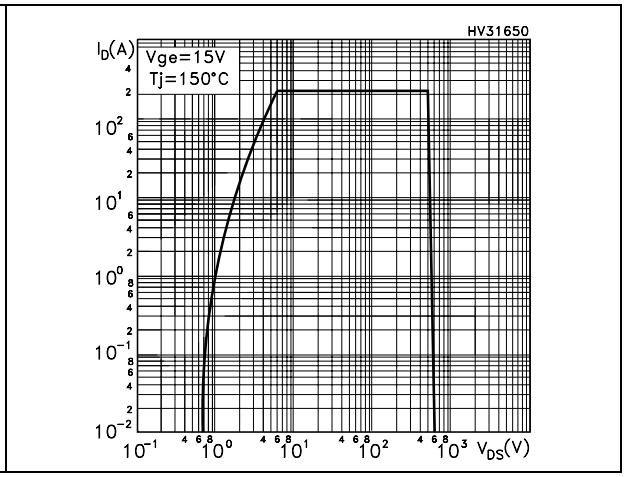
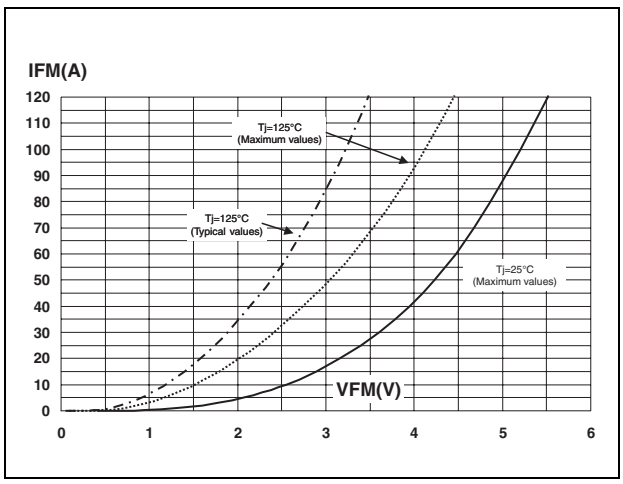


Figure 16. Emitter-collector diode characteristics



3 Test circuit

Figure 17. Test circuit for inductive load switching

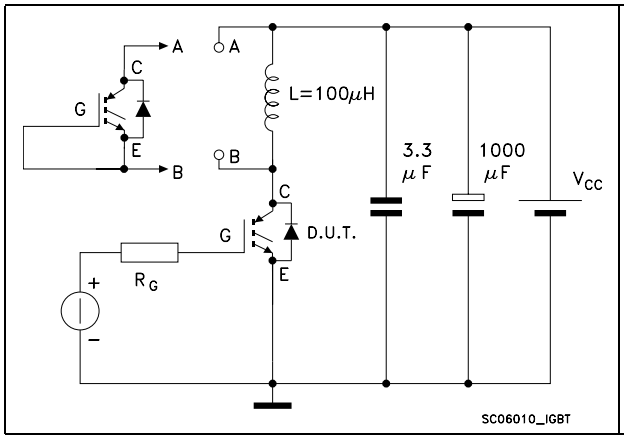


Figure 18. Gate charge test circuit

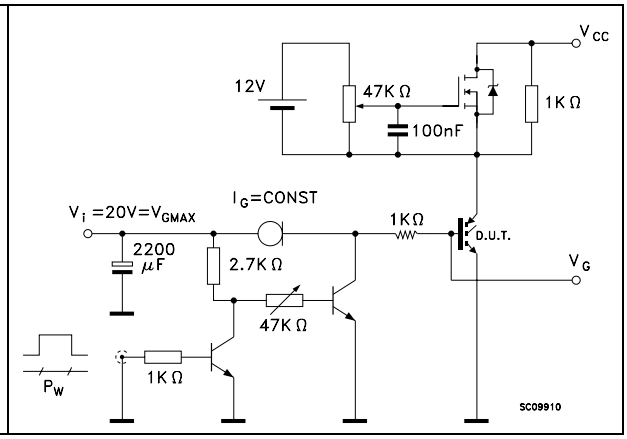


Figure 19. Switching waveforms

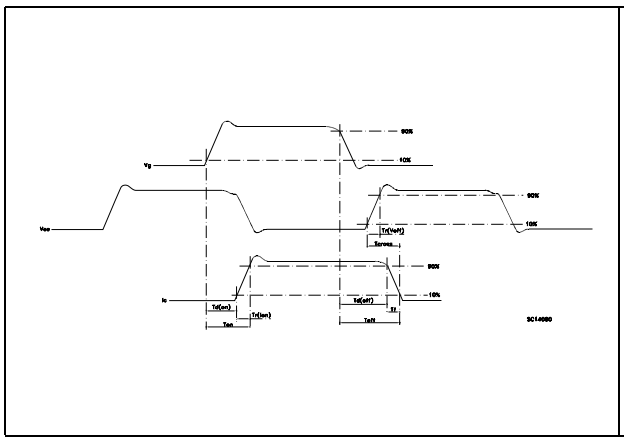
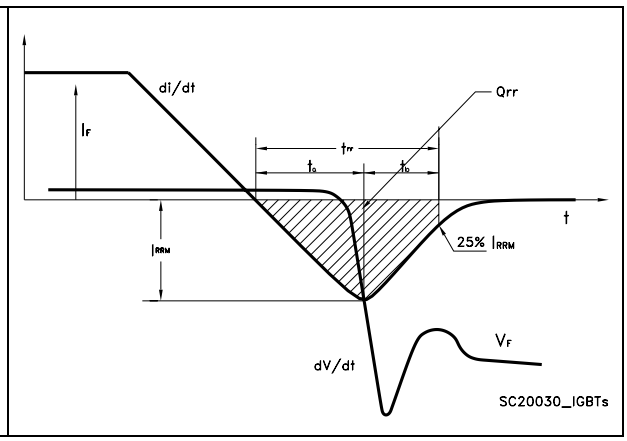


Figure 20. Diode recovery times waveform

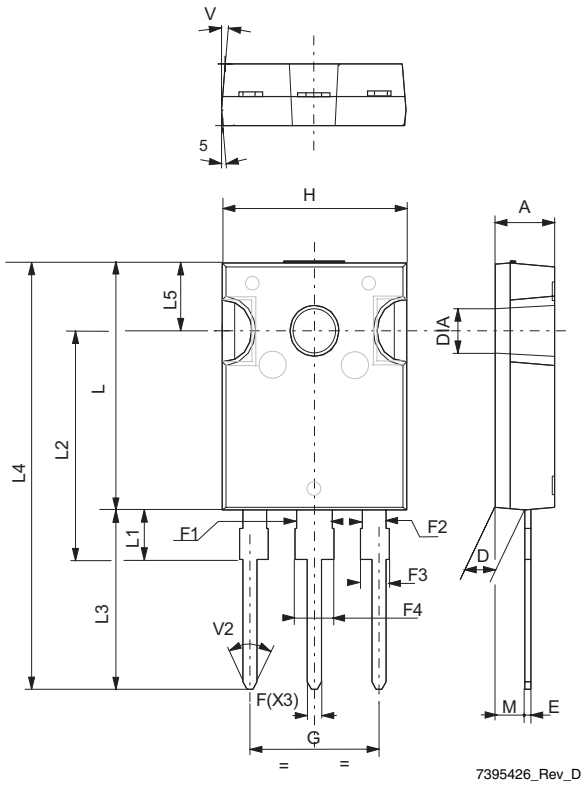


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.16
D	2.2		2.6
E	0.4		0.8
F	1		1.4
F1		3	
F2		2	
F3	1.9		2.4
F4	3		3.4
G		10.9	
H	15.45		16.03
L	19.85		21.09
L1	3.7		4.3
L2	18.3		19.13
L3	14.2		20.3
L4	34.05		41.38
L5	5.35		6.3
M	2		3
V		5°	
V2		60°	
DIAM	3.55		3.65



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
05-Jun-2008	1	First release

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST’s terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST’S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER’S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com